

Data sheet 2L30_SU22_NW-A

Active area: 30 x 30 mm²

Chip area: 34 x 34 mm²

Characteristics	Min.	Typ.	Max.	Unit
Position non-linearity		0,3	0,8	% (±)
Detector resistance	7	10	16	kΩ
Leakage current		200	2000	nA
Noise current		1,3	2,5	pA/√Hz
Responsivity		0,67		A/W
Capacitance		850	955	pF
Rise time (10%-90%)		3	7	μs
Bias voltage (reverse)	5	15	30	V
Thermal drift		40	200	ppm/°C

Maximum ratings

Reverse voltage	30	V
Operating temperature	70	°C
Storage temperature	100	°C

Test conditions: Room temperature 23 °C, bias voltage 15V, light source wavelength 655 nm. Position non-linearity and thermal drift are valid within 80 % of the detector length.

Package: Ceramic substrate without window, 47 x 36 mm², with four soldered cables. Bondwires protected by epoxy.

Date

2002-09-09

